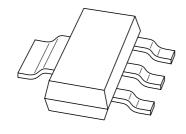
# DISCRETE SEMICONDUCTORS

# DATA SHEET



# **PZT2222A**NPN switching transistor

Product data sheet Supersedes data of 1997 Jun 02 1999 Apr 14



# **NPN** switching transistor

**PZT2222A** 

#### **FEATURES**

- High current (max. 600 mA)
- Low voltage (max. 40 V).

#### **APPLICATIONS**

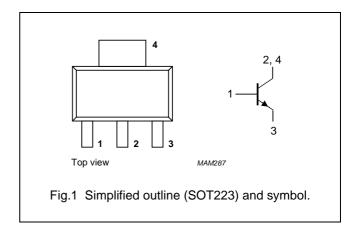
· Switching and linear amplification.

#### **DESCRIPTION**

NPN switching transistor in a SOT223 plastic package. PNP complement: PZT2907A.

#### **PINNING**

PIN	DESCRIPTION
1	base
2, 4	collector
3	emitter



#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	75	V
$V_{CEO}$	collector-emitter voltage	open base	_	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	6	V
I <sub>C</sub>	collector current (DC)		_	600	mA
I <sub>CM</sub>	peak collector current		_	800	mA
I <sub>BM</sub>	peak base current		_	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	1.15	W
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

# NPN switching transistor

PZT2222A

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	109	K/W
R <sub>th j-s</sub>	thermal resistance from junction to soldering point		28	K/W

#### Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see *"Thermal considerations for SOT223 in the General Part of associated Handbook"*.

#### **CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

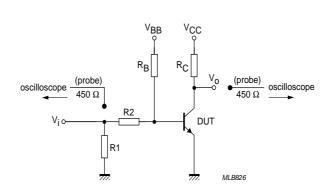
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 60 V	_	10	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 60 V; T <sub>amb</sub> = 125 °C	_	10	μΑ
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V	_	10	nA
h <sub>FE</sub>	DC current gain	$I_C = 0.1 \text{ mA}; V_{CE} = 10 \text{ V}$	35	_	
		$I_C = 1 \text{ mA}; V_{CE} = 10 \text{ V}$	50	_	
		$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V}$	75	_	
		$I_C = 10 \text{ mA}; V_{CE} = 10 \text{ V};$ $T_{amb} = -55 \text{ °C}$	35	_	
		I <sub>C</sub> = 150 mA; V <sub>CE</sub> = 1 V; note 1	50	_	
		I <sub>C</sub> = 150 mA; V <sub>CE</sub> = 10 V; note 1	100	300	
		I <sub>C</sub> = 500 mA; V <sub>CE</sub> = 10 V; note 1	40	_	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA	_	300	mV
		I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA	_	1	V
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 150 mA; I <sub>B</sub> = 15 mA	0.6	1.2	V
		$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	_	2	٧
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	_	8	pF
C <sub>e</sub>	emitter capacitance	$I_C = i_C = 0$ ; $V_{EB} = 500 \text{ mV}$ ; $f = 1 \text{ MHz}$	_	25	pF
f <sub>T</sub>	transition frequency	$I_C = 20 \text{ mA}; V_{CE} = 20 \text{ V}; f = 100 \text{ MHz}$	300	_	MHz
Switching t	imes (between 10% and 90% levels	); (see Fig.2)			
t <sub>on</sub>	turn-on time	I <sub>Con</sub> = 150 mA; I <sub>Bon</sub> = 15 mA;	_	35	ns
t <sub>d</sub>	delay time	$I_{Boff} = -15 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	_	10	ns
t <sub>r</sub>	rise time		_	25	ns
t <sub>off</sub>	turn-off time		_	250	ns
t <sub>s</sub>	storage time		_	200	ns
t <sub>f</sub>	fall time		_	60	ns

#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

# NPN switching transistor

PZT2222A



$$\begin{split} &V_i = 9.5 \; V; \; T = 500 \; \mu s; \; t_p = 10 \; \mu s; \; t_r = t_f \leq 3 \; n s. \\ &R1 = 68 \; \Omega; \; R2 = 325 \; \Omega; \; R_B = 325 \; \Omega; \; R_C = 160 \; \Omega. \\ &V_{BB} = -3.5 \; V; \; V_{CC} = 29.5 \; V. \\ &Oscilloscope input impedance \; Z_i = 50 \; \Omega. \end{split}$$

Fig.2 Test circuit for switching times.

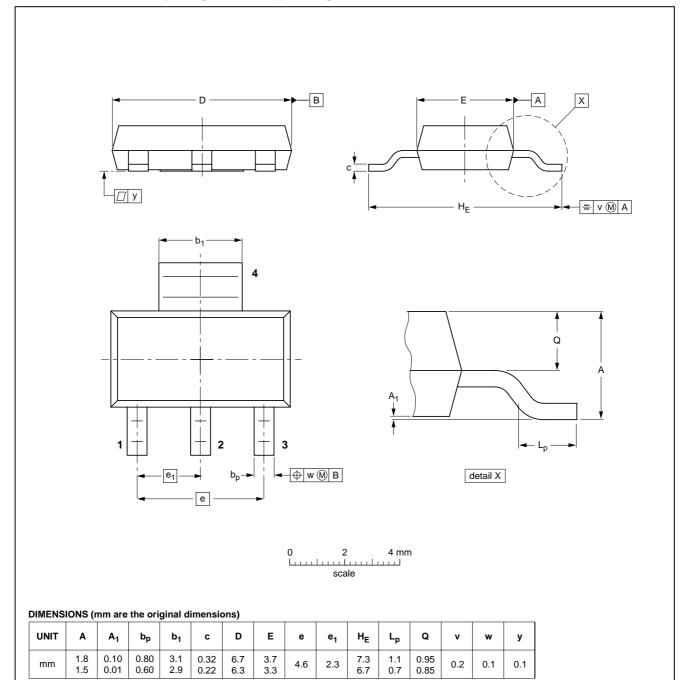
# NPN switching transistor

PZT2222A

**PACKAGE OUTLINE** 

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

**SOT223** 



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT223			SC-73			<del>97-02-28</del> 99-09-13

## NPN switching transistor

PZT2222A

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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6

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1999 Apr 14

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#### **Contact information**

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